

SUBSTRATE PROCESSING METHOD, METHOD FOR PRODUCING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A substrate processing method according to the present invention comprises: (a) a step for supplying an adsorption inhibition gas to a substrate; (b) a step for supplying a starting material gas to the substrate; (c) a step for supplying a reaction gas to the substrate; and (d) a step for forming a film of the elements contained in the starting material gas on the substrate by performing the steps (a), (b) and (c) a predetermined number of times in a state where the amount of the starting material gas supplied in the step (b) to be exposed to the substrate is set higher than the amount of the adsorption inhibition gas supplied in the step (a) to be exposed to the substrate.

Fig. 4